





LOW POWER FRONT-END ELECTRONICS FOR HYBRID PIXEL DETECTORS

~ Master Degree in Physics of Advanced Technologies ~

SUPERVISOR

Prof. Angelo Rivetti

<u>CANDIDATE</u>

Olave Elias Jonhatan





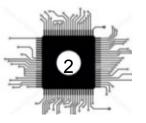
CONTEXT

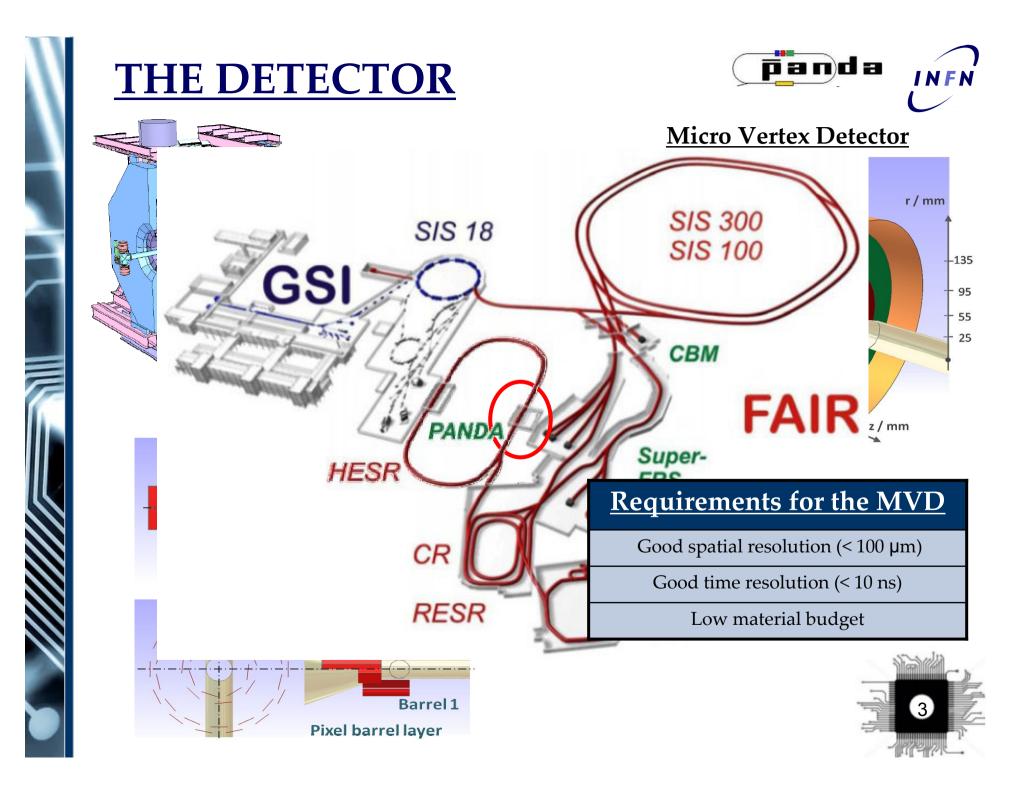
Developement for the panda Detector

WORK TOPIC

Design of a new Digital to Analog Converter for the ASIC

Study of a new technology for the ASIC

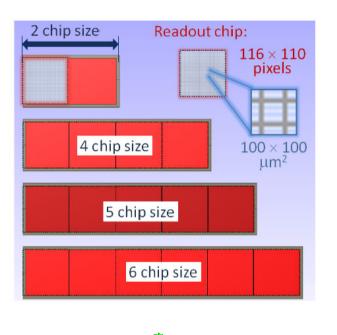






HYBRID PIXEL DETECTORS





ASIC Requirements

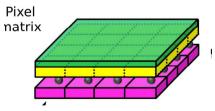
Measurements	Hit position Energy loss Time
Pixel Size	100 μm x 100 μm
Time/charge digitization	At pixel level
ASIC Size	Fixed by the pixel size
Input Polarity	Selectable
Trigger	Self triggering
Power Consumption	< 20 µw

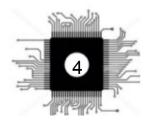
116 rows 110 cols

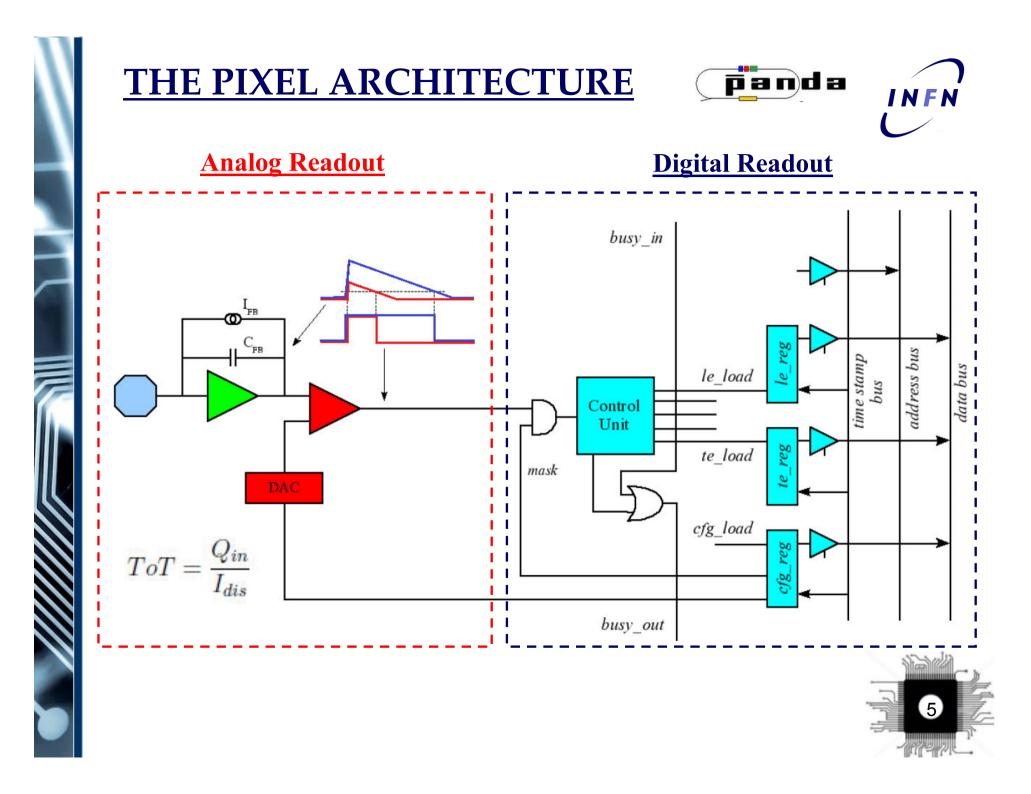
More channels are required

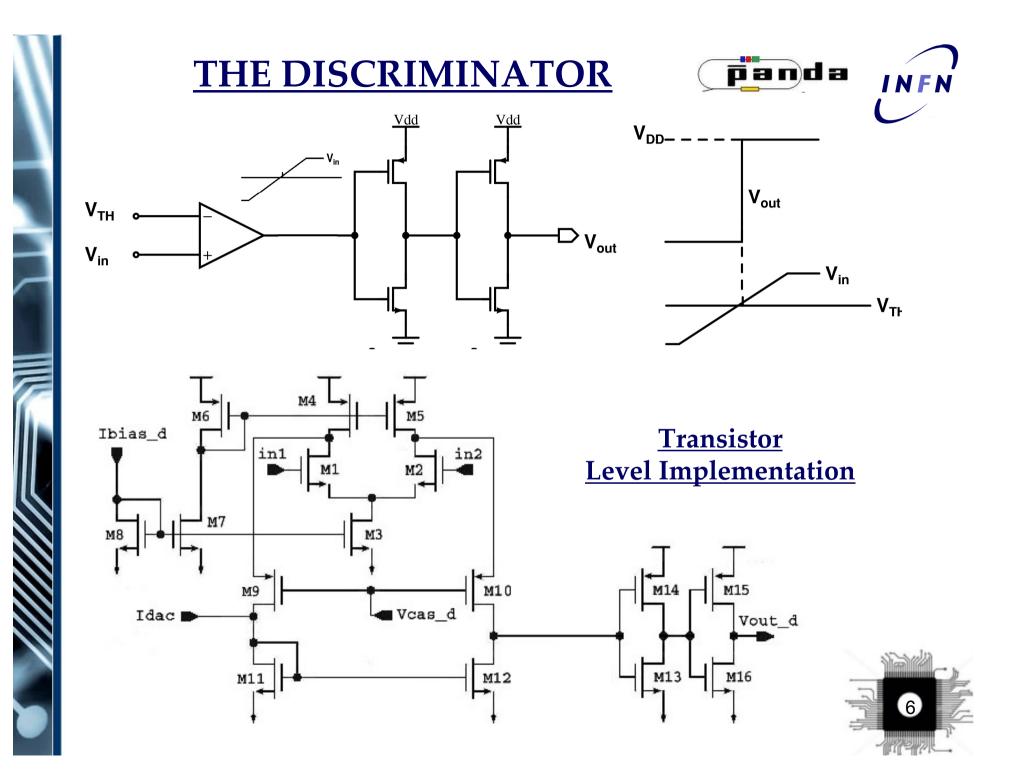
The compact design allow to optain a very good resolution also with high rates

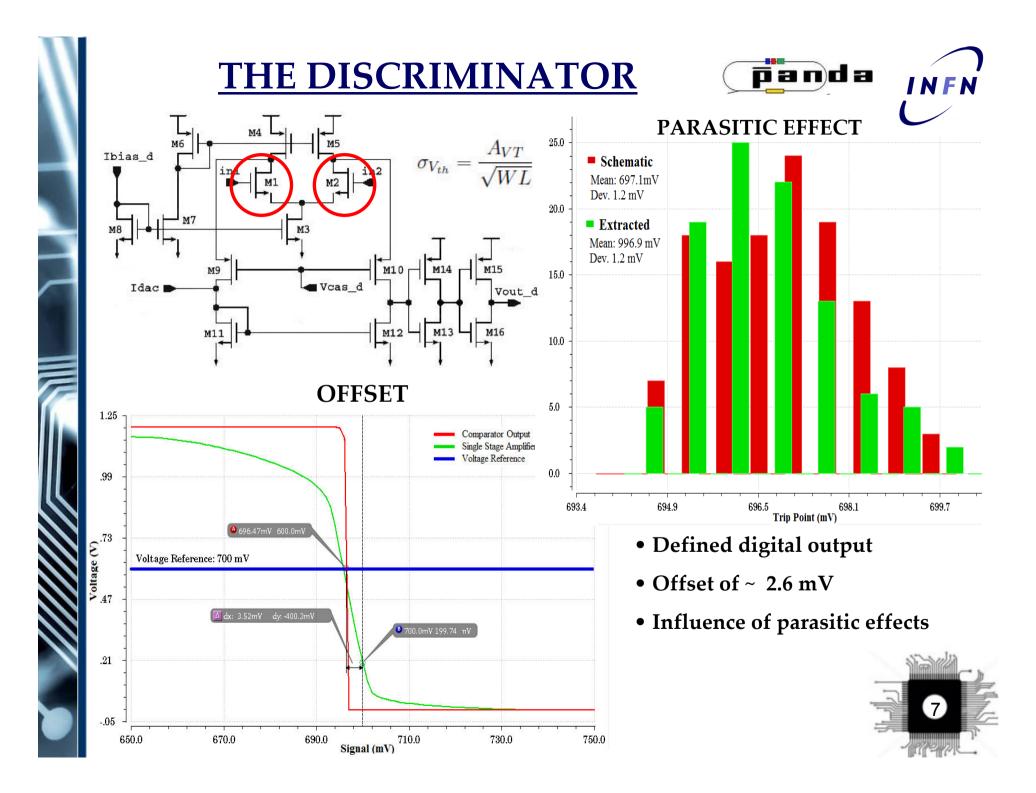
Thinned silicon Cz substrate Epitaxial silicon layer Bump bonding Readout chip Carbon foam Carbon fiber Cooling system

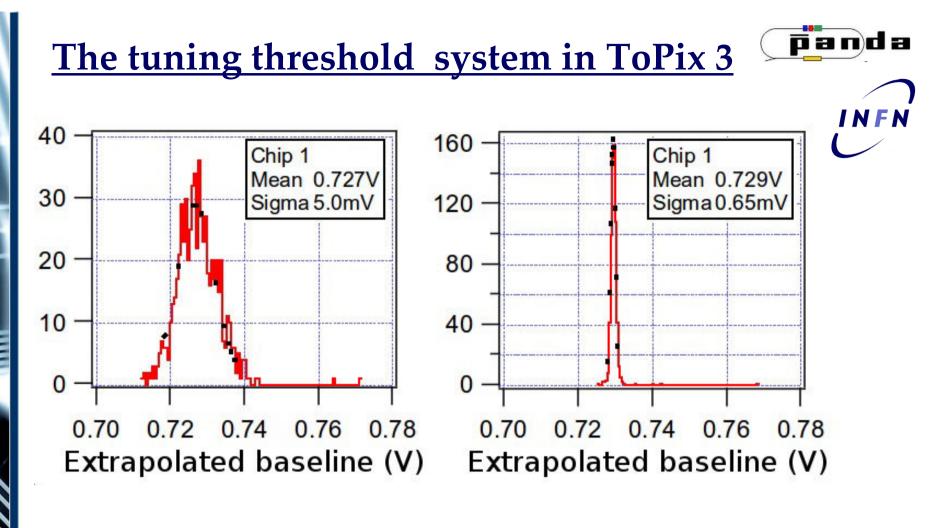








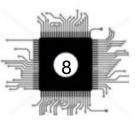


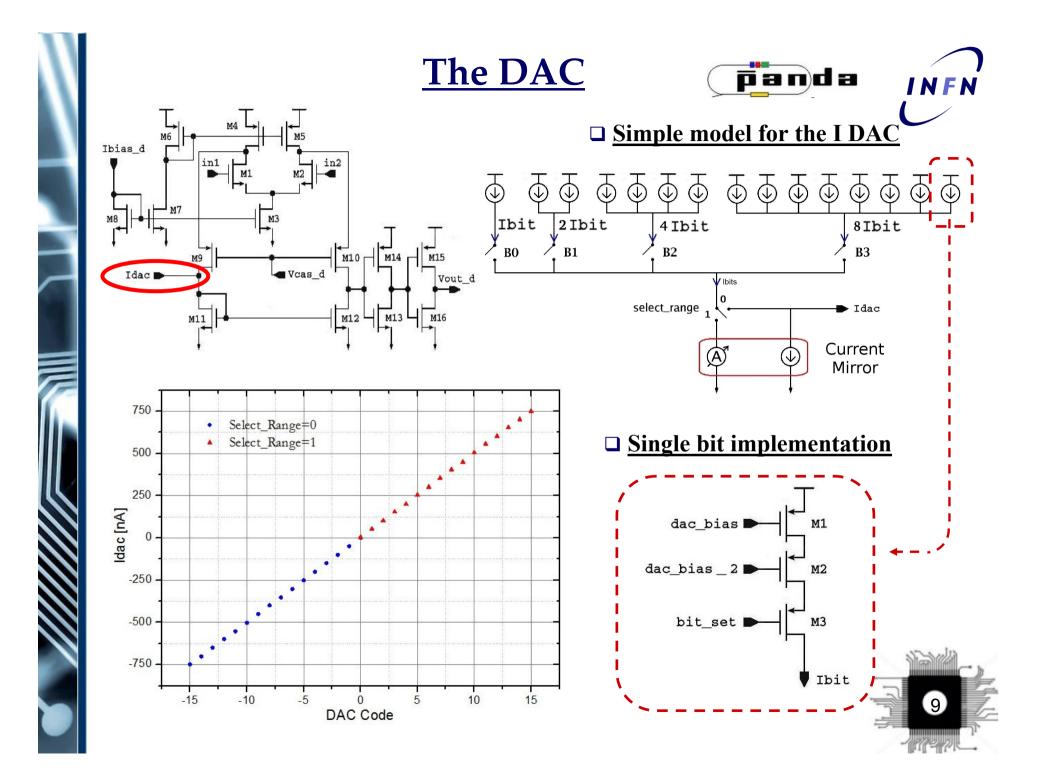


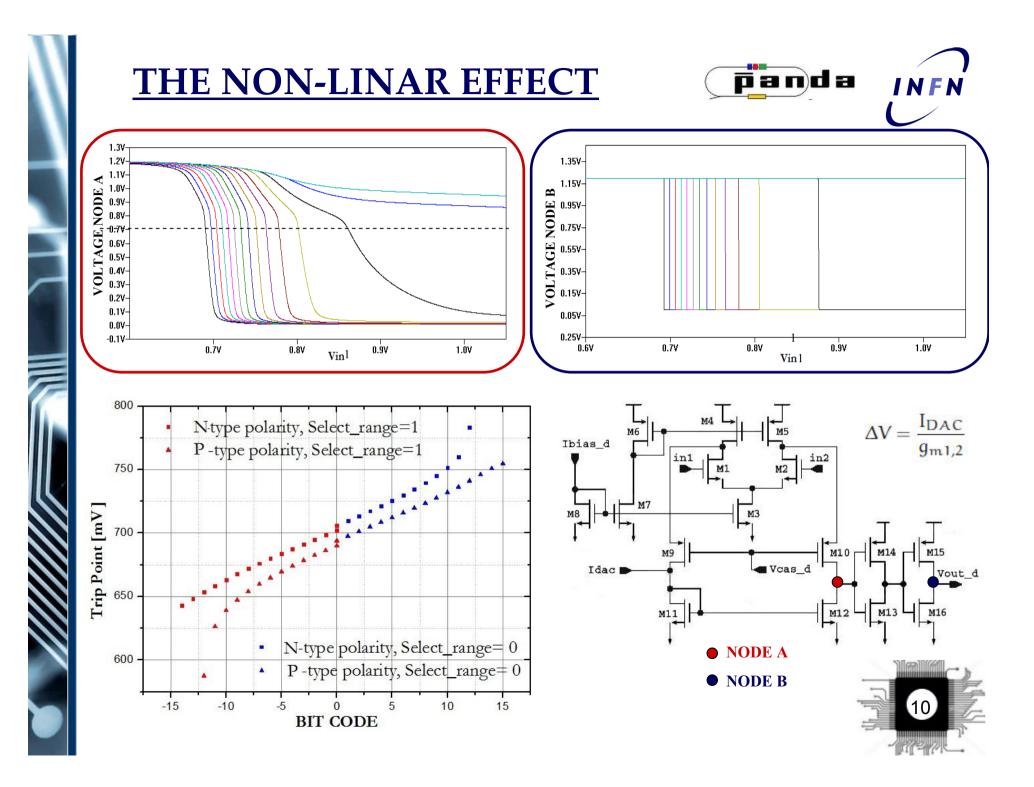
The system allows a good correction

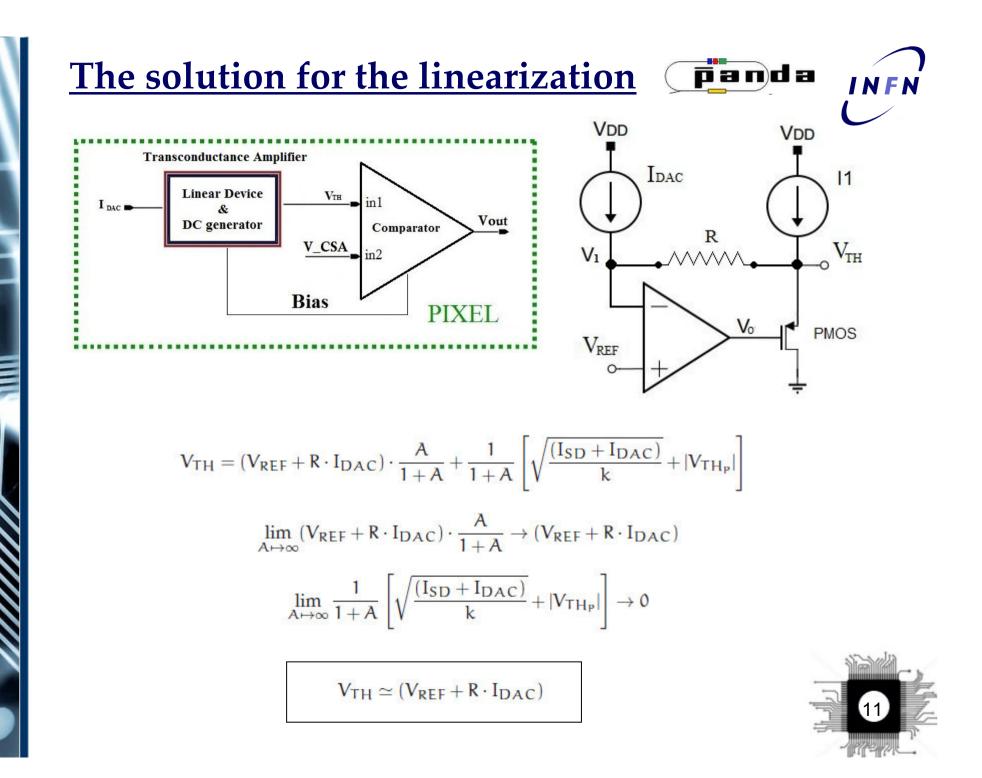
Due to a non-linear response the tuning procedure appears cumbersome

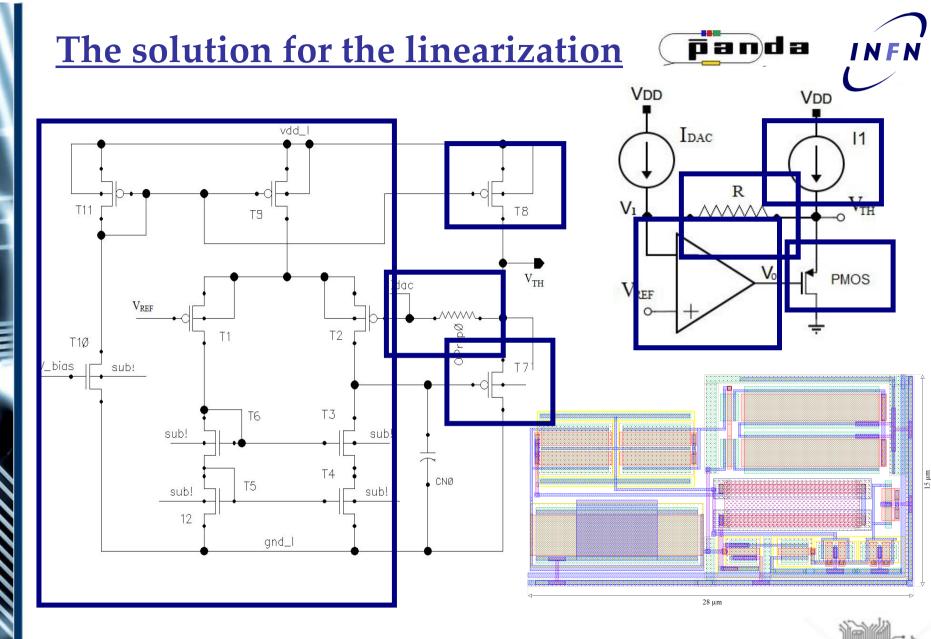
The devices involved are: COMPARATOR & DAC



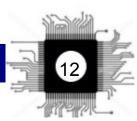


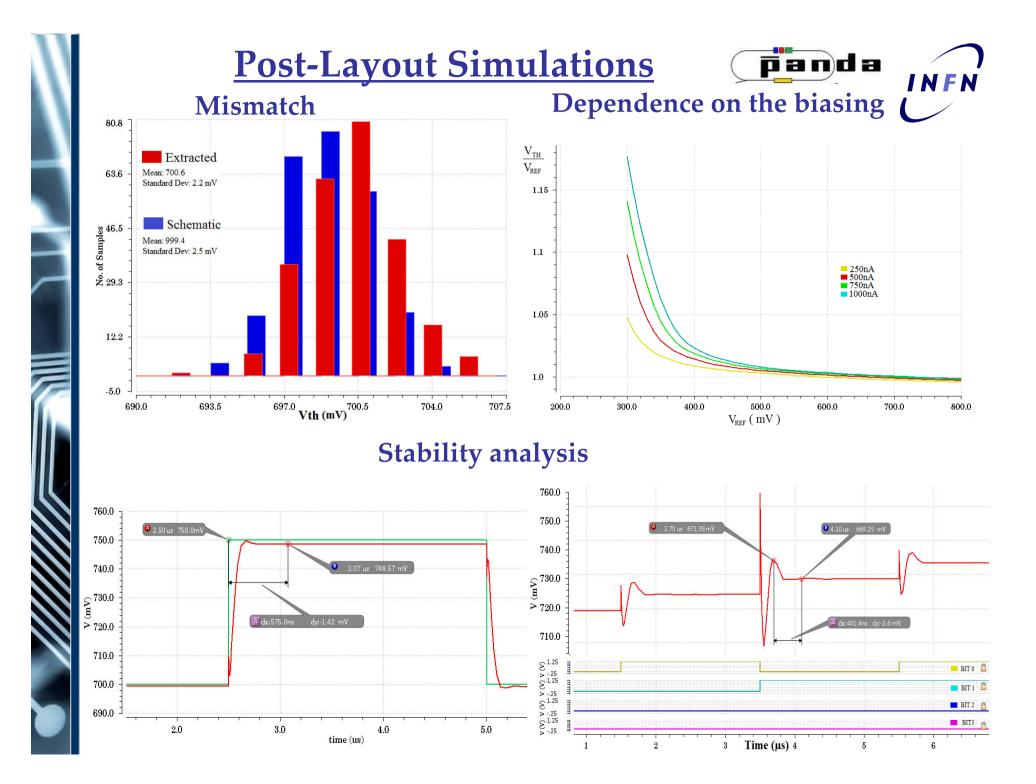


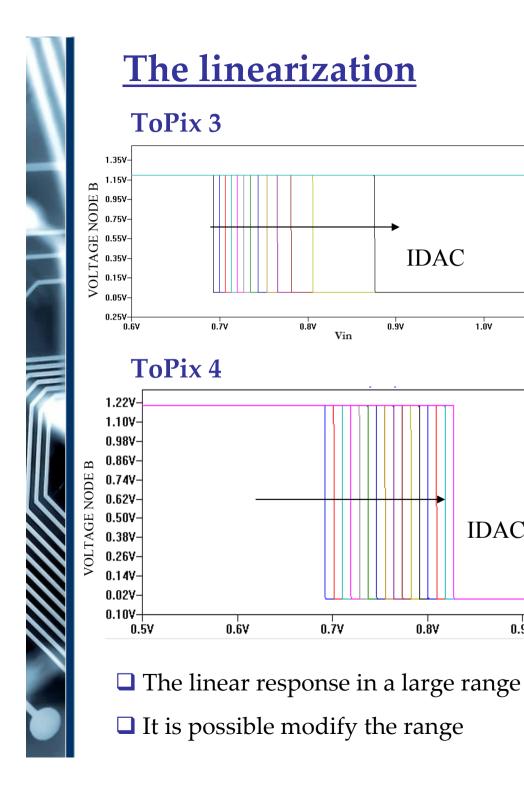




Some trade-offs are necessary to fit the circuit in the available area.



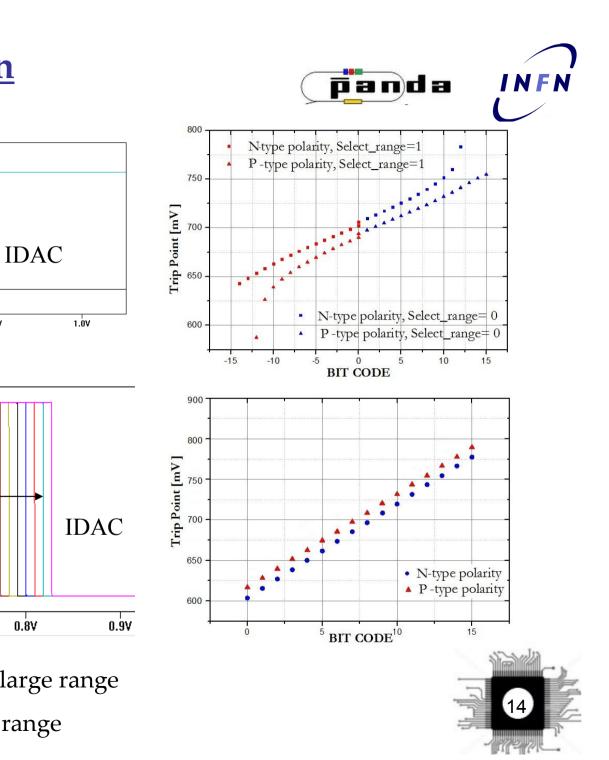


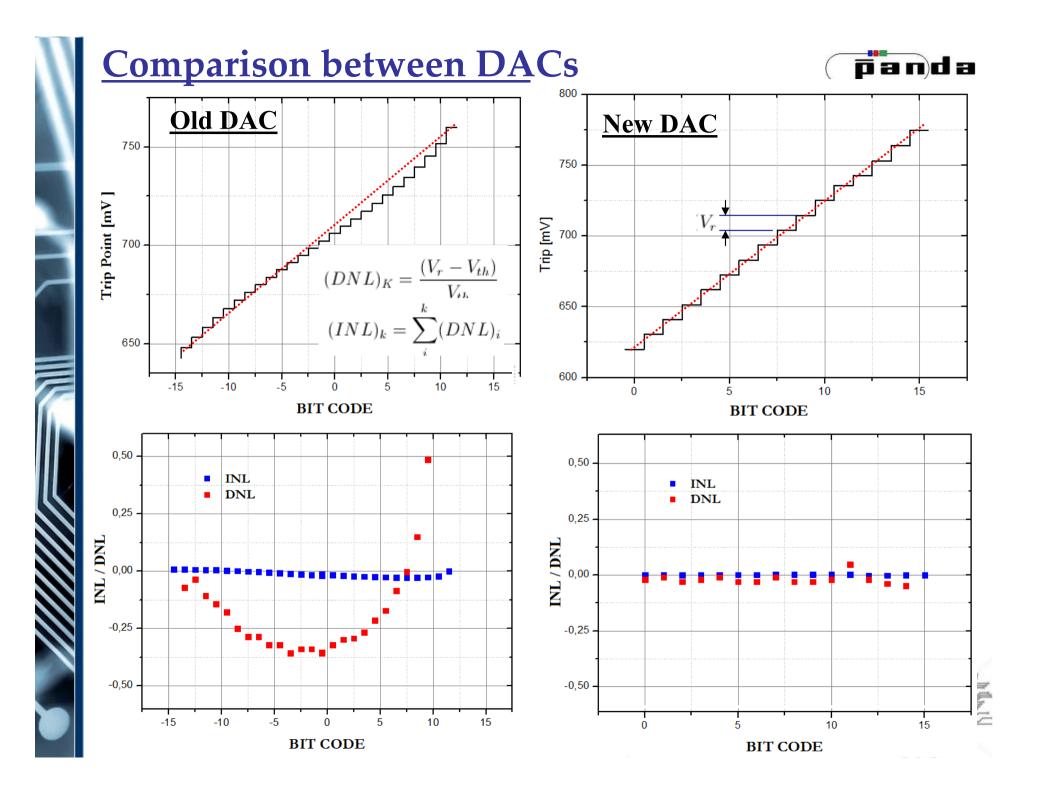


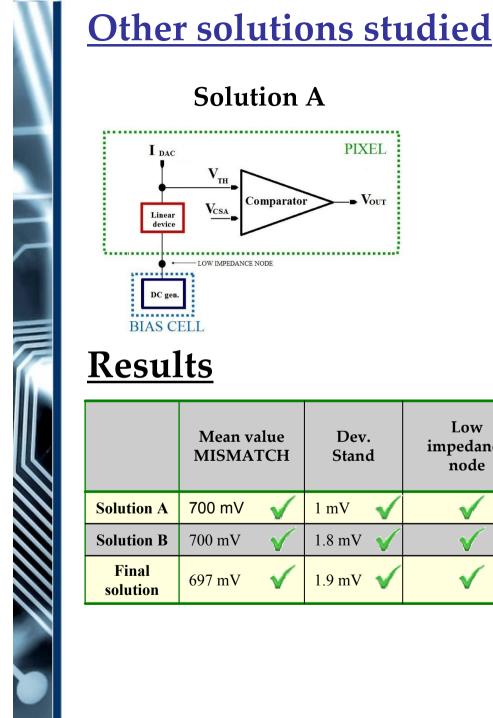
0.9V

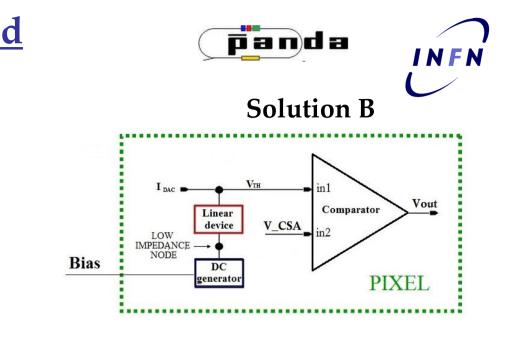
Vin

0.77









Results

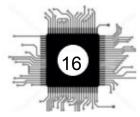
V_{TH}

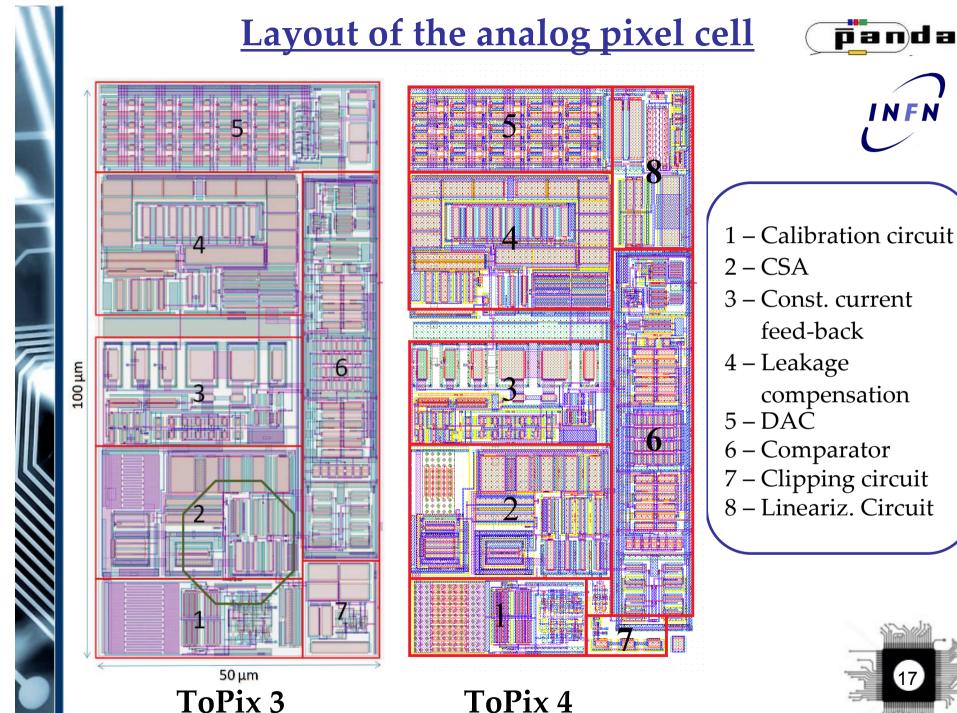
Comparator

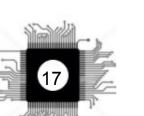
	Mean value MISMATCH	Dev. Stand	Low impedance node	Homogeneity in different pixels	External bias	DAC protection
Solution A	700 mV 🛛 🗸	1 mV 🗸	✓	X	X	X
Solution B	700 mV 🛛 🗸	1.8 mV 🗸	 ✓ 	✓	X	X
Final solution	697 mV 🛛 💙	1.9 mV 🗸	 ✓ 	\checkmark	v	\checkmark

PIXEL

- Vout







1 – Calibration circuit

INFN

- 3 Const. current
- 6 Comparator
- 7 Clipping circuit
- 8 Lineariz. Circuit





Current Technology A 0.13 μm

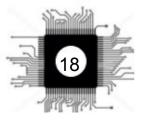
More flavors of devices
High cost

□ Proposed Technology B 0.11 µm

Less flavor of devices
Reduced cost

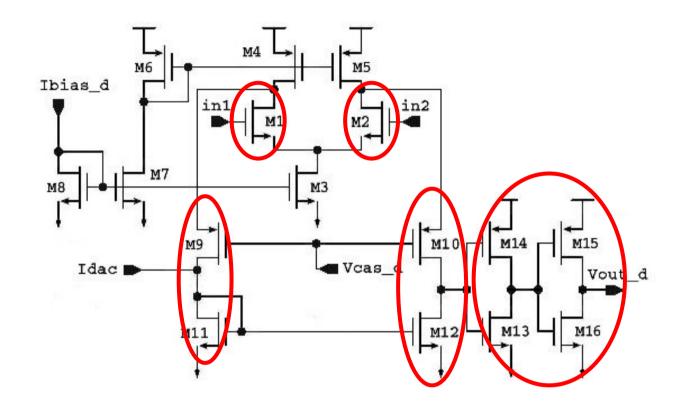


Gate oxide Drain terminal P Type N Type N Type





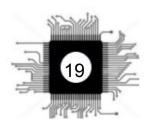
Study of the new technology



Three configurations

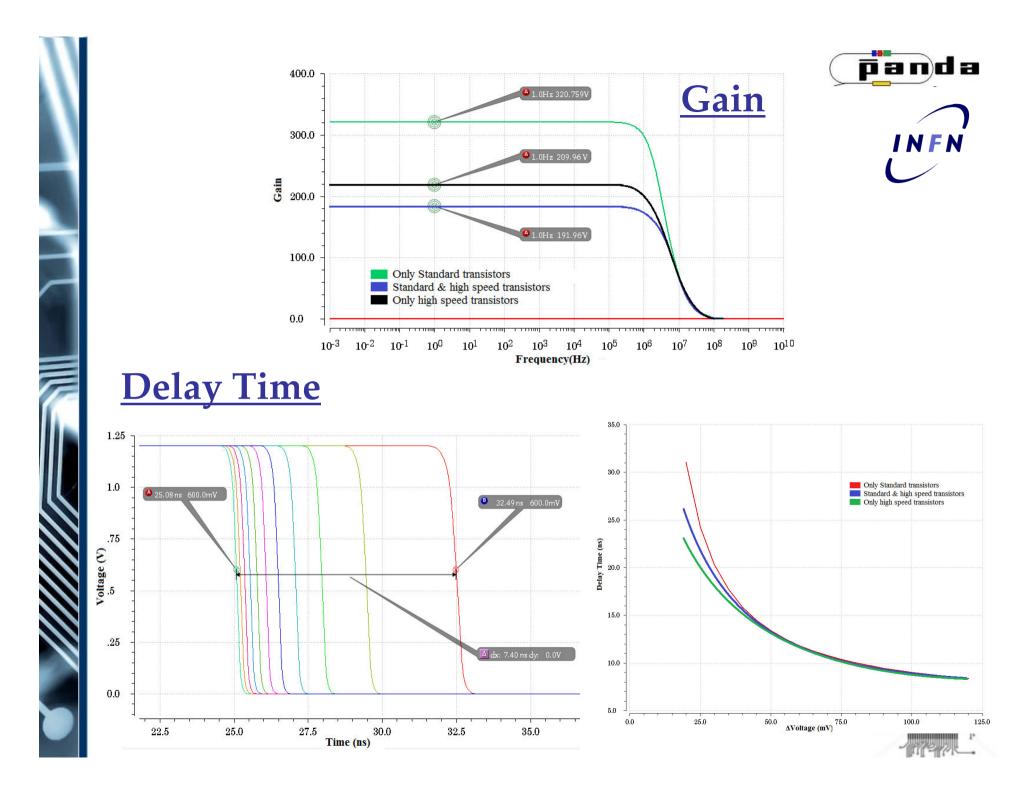
- Standard transistors
- High speed transistors and Stantard Transistors
- All High speed transistors

- **The analysis**
 - ≻ Gain
 - ≻ Offset
 - Delay time



p a n d a

INFN



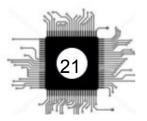


<u>Results</u>

COMPARISON OF TECHNOLOGIES Technology A **Technology B** Stand. & High Speed Param. Standard Standard **High Speed** Trip[mV] 697 699 699 700 Gain 70 191 209 320 Delay[ns] 11 24 22 20 Delay'[ns] 8 8 8 5

□ <u>THE NEW TECHNOLOGY ALLOWS TO OBTAIN;</u>

- ➢ Higher gain
- Better control voltage
- ➢ Higher delay time





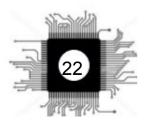
INFN

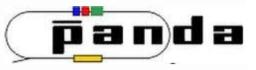


CONCLUSIONS

• The solution for the tuning system has been found

- In Novembre 2013 ToPix 4 with the improvement realized was submitted to the foundry for fabrication.
- The analysis of the new technology shows good results for the comparator.
- The study of the new technology for the whole ASIC needs more studies.





Thank you for your attention!

INFN



716

(MA) 714 (MA) 714 (MA) 712 (MA) 710 (MA

708

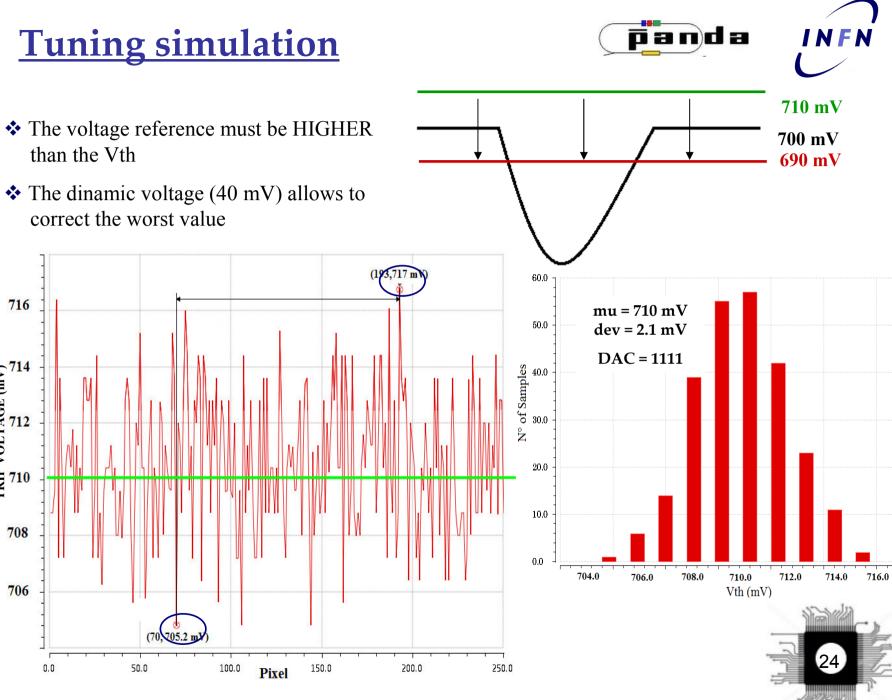
706

0.0

50.0

Tuning simulation

than the Vth

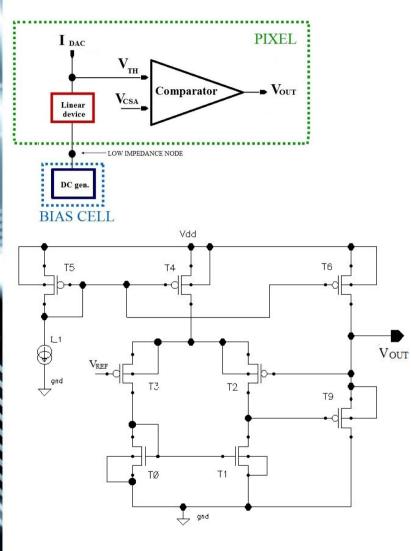


Other solutions studied

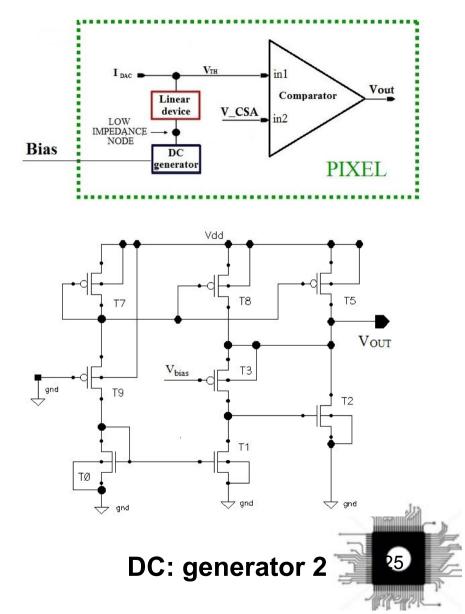


Solution A

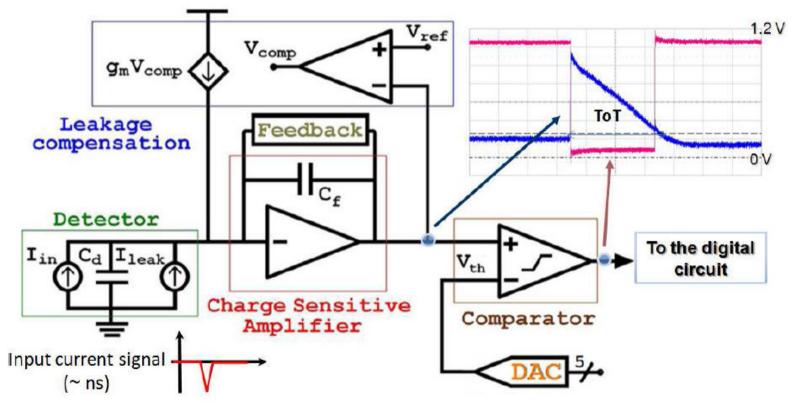


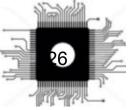


DC: generator 1



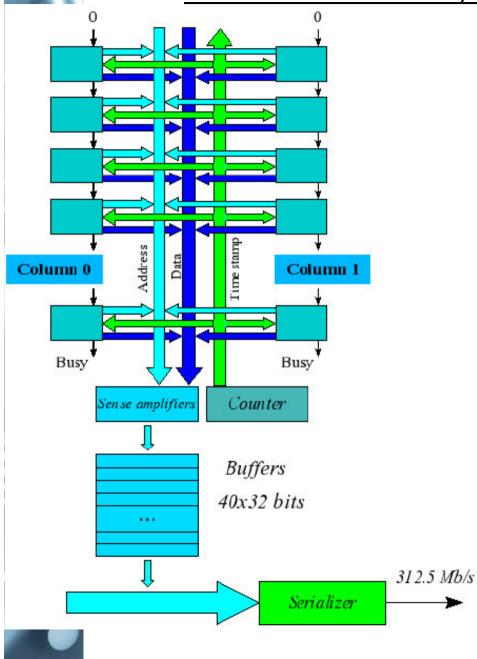
The analogue pixel Architecture





The ASIC for Hybrid Pixel Detectors

-



Measurements	Hit position Energy loss Time
Pixel Size	100 μm x 100 μm
Time/charge digitization	At pixel level
ASIC Size	Fixed by the pixel size
Input Polarity	Selectable
System Clock	155.52 MHz
Time resolution	<10 ns
Trigger	Self triggering
Power Consumption	$< 20 \ \mu W$
Noise Level	200 e ⁻ rms
Linear dynamic range	Up to 50 fC

